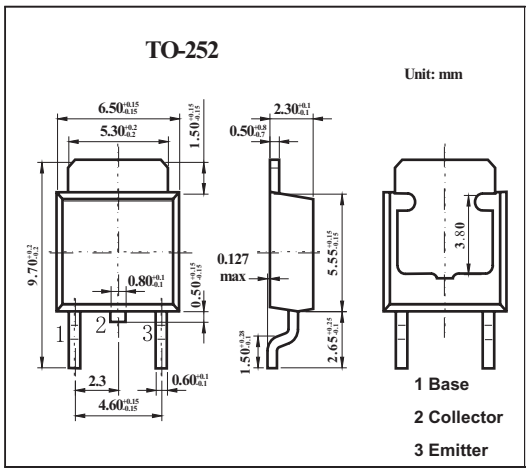
Silicon PNP Transistor

2SB768



Features

- High Voltage:V_{CBO}=-150V

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-to-Base Voltage	V_{CBO}	-200	V
Collector-to-Emitter Voltage	V_{CEO}	-150	V
Emitter-to-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Collector Current (Pulse) *1	I_{CP}	-3	A
Total Power Dissipation *2 Ta=25℃	P_T	2	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

*1 PW≤10ms,.Duty Cycle≤50%

*2 when mounted on ceramic substrate of 7.5cm^2 X 0.7mm

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=-150V, I_E=0			-50	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-4V, I_C=0			-50	μA
DC Current Gain *	h_{FE}	V_{CE}=-10V, I_C=-0.4A	40	80	200	
Collector-to-Emitter Saturation Voltage *	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA		-0.15	-1.0	V
Gain Badnwidth Product	f_T	V_{CE}=-10V,I_E=-0.4mA		10		MHz

* Pulsed :pw≤350μs,Duty Cycle≤2%

h_{FE} Classification

Marking	M	L	K
hFE	40 to 80	60 to 120	100 to 200